

DESCRIPTION

The CNX48U, H11BX, MOC8080 and TIL113 have a gallium arsenide infrared emitter optically coupled to a silicon planar photodarlington.

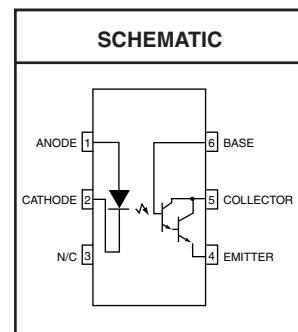
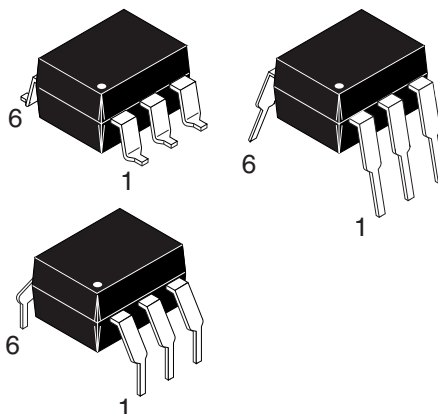
CNX48U	H11B1	H11B2	H11B255	H11B3
MOC8080	TIL113			

FEATURES

- High sensitivity to low input drive current
- Meets or exceeds all JEDEC Registered Specifications
- VDE 0884 approval available as a test option
-add option .300. (e.g., H11B1.300)

APPLICATIONS

- Low power logic circuits
- Telecommunications equipment
- Portable electronics
- Solid state relays
- Interfacing coupling systems of different potentials and impedances.



Parameter	Symbol	Device	Value	Units
TOTAL DEVICE				
Storage Temperature	T _{STG}	All	-55 to +150	°C
Operating Temperature	T _{OPR}	All	-55 to +100	°C
Lead Solder Temperature	T _{SOL}	All	260 for 10 sec	°C
Total Device Power Dissipation @ T _A = 25°C Derate above 25°C	P _D	All	250	mW
			3.3	mW/°C
EMITTER				
Continuous Forward Current	I _F	All	100	mA
Reverse Voltage	V _R	All	6	V
Forward Current - Peak (300 μs, 2% Duty Cycle)	I _{F(pk)}	All	3.0	A
LED Power Dissipation @ T _A = 25°C Derate above 25°C	P _D	All	100	mW
			1.8	mW/°C
DETECTOR				
Collector-Emitter Breakdown Voltage	BV _{CEO}	CNX48U, TIL113	30	V
		H11B1, H11B2 H11B3	25	
		H11B255 MOC8080	55	
Collector-Base Breakdown Voltage	BV _{CBO}	CNX48U, H11B1 H11B2, H11B3 TIL113	30	V
		H11B255 MOC8080	55	V
Emitter-Collector Breakdown Voltage	BV _{ECO}	All	7	V
Detector Power Dissipation @ T _A = 25°C Derate above 25°C	P _D	All	150	mW
			2.0	mW/°C

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ELECTRICAL CHARACTERISTICS (T_A = 25°C Unless otherwise specified.)

INDIVIDUAL COMPONENT CHARACTERISTICS

Parameter	Test Conditions	Symbol	Device	Min	Typ**	Max	Unit
EMITTER Input Forward Voltage	(I _F = 10 mA)	V _F	H11B1, H11B2 H11B255 MOC8080 TIL113	0.8	1.2	1.5	V
	(I _F = 10 mA)		CNX48U		1.2	1.3	
	(I _F = 10 mA, T _A = -55°C)		MOC8080	0.9	1.3	1.7	
	(I _F = 10 mA, T _A = 100°C)			0.7	1.05	1.4	
	(I _F = 50 mA)		H11B3		1.35	1.5	
Reverse Leakage Current	(V _R = 6 V)	I _R	All		0.001	10	μA
Capacitance	(V _F = 0 V, f = 1.0 MHz)	C	All		50		pF
DETECTOR Collector-Emitter Breakdown Voltage	(I _C = 1 mA, I _F = 0)	BV _{CEO}	CNX48U	30	60		V
	(I _C = 100 μA, I _F = 0)		TIL113				
	(I _C = 10 mA, I _F = 0)		H11B1, H11B2 H11B3	25	60		
	(I _C = 100 μA, I _F = 0)		H11B255	55	70		
	(I _C = 1 mA, I _F = 0)		MOC8080				
Collector-Base Breakdown Voltage	(I _C = 100 μA, I _E = 0)	BV _{CBO}	CNX48U, H11B1 H11B2, H11B3 TIL113	30	100		V
	(I _C = 100 μA, I _F = 0)		H11B255 MOC8080	55	100		
Emitter-Collector Breakdown Voltage	(I _E = 100 μA, I _B = 0)	BV _{ECO}	All	7	10		V
Collector-Emitter Dark Current	(V _{CE} = 10 V, Base Open)	I _{CEO}	All		1	100	nA

Note

** Typical values at T_A = 25°C

CNX48U	H11B1	H11B2	H11B255	H11B3
MOC8080	TIL113			

TRANSFER CHARACTERISTICS (T_A = 25°C Unless otherwise specified.)

DC Characteristics	Test Conditions	Symbol	Device	Min	Typ**	Max	Units
Collector Output Current ⁽¹⁾	(I _F = 10 mA, V _{CE} = 5 V)	I _C (CTR)	MOC8080	50 (500)			mA (%)
			H11B255	10 (100)			
	(I _F = 10 mA, V _{CE} = 1 V)		CNX48U	60 (600)			
			TIL113	30 (300)			
	(I _F = 1 mA, V _{CE} = 5 V)		H11B1	5 (500)			
			H11B2	2 (200)			
			H11B3	1 (100)			
	(I _F = 1 mA, V _{CE} = 1 V)		CNX48U	5 (500)			
	(I _F = 0.5 mA, V _{CE} = 1 V)			1.75 (350)			
Saturation Voltage	(I _F = 1 mA, I _C = 1 mA)	V _{CE(sat)}	H11B1, H11B2 H11B3, MOC8080			1.0	V
	(I _F = 5 mA, I _C = 10 mA)		CNX48U			1.0	
	(I _F = 50 mA, I _C = 50 mA)		H11B255			1.0	
	(I _F = 8 mA, I _C = 2 mA)		TIL113			1.25	
AC Characteristics	(I _C = 10 mA, V _{CE} = 10 V) (R _L = 100 Ω) (Fig.7)	t _{on}	H11B1 H11B2		25		μs
		t _{off}	H11B255 H11B3		18		
	(I _F = 10 mA, V _{CC} = 5 V) (R _E = 100 Ω), (R _{BE} = 1MΩ) (Fig. 8)	t _{on}	CNX48U		3.5		
		t _{off}			36		
	(I _F = 1 mA, V _{CC} = 5 V) (R _E = 1kΩ), (R _{BE} = 10MΩ) (Fig. 8)	t _{on}			70		
		t _{off}			190		
	(I _F = 5 mA, V _{CC} = 10 V) (R _L = 100 Ω) (Fig.7)	t _{on}	MOC8080		3.5		
		t _{off}			25		
	(I _F = 200 mA, I _C = 50 mA) (V _{CC} = 10 V) (R _L = 100 Ω) (Fig.7)	t _{on}	TIL113		0.35	5	
		t _{off}			55	100	

ISOLATION CHARACTERISTICS

Characteristic	Test Conditions	Symbol	Min	Typ**	Max	Units
Input-Output Isolation Voltage ⁽²⁾	(I _{I-O} ≤ 1 μA, V _{rms} , t = 1 min.)		5300			Vac(rms)
Isolation Resistance ⁽²⁾	(V _{I-O} = 500 VDC)	R _{ISO}		10 ¹¹		Ω
Isolation Capacitance ⁽²⁾	(V _{I-O} = ∅, f = 1 MHz)	C _{ISO}		0.8		pf

Note

** Typical values at T_A = 25°C

CNX48U H11B1 H11B2 H11B255 H11B3
MOC8080 TIL113

Fig. 1 Output Current vs. Input Current

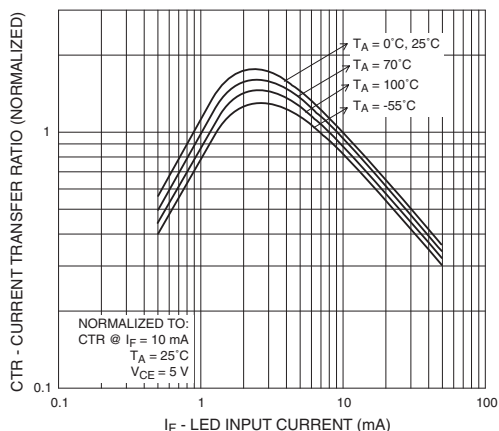


Fig. 2 Current Transfer Ratio vs. Ambient Temperature

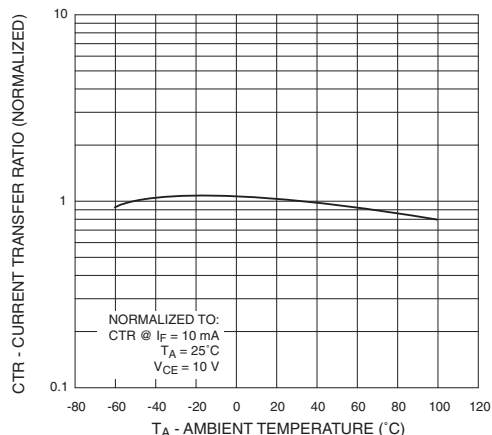


Fig. 3 Collector Current vs. Collector-Emitter Voltage

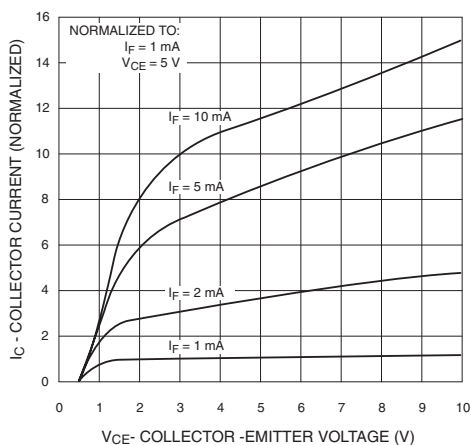


Fig. 4 Dark Current vs. Ambient Temperature

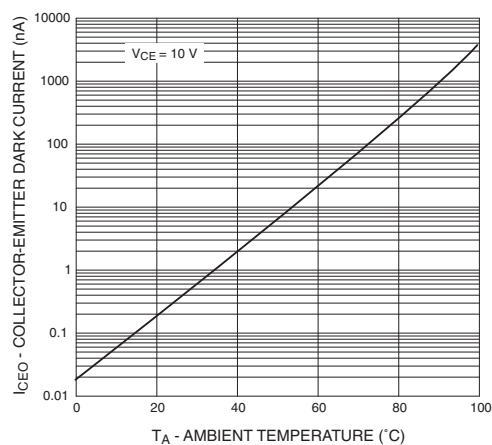


Fig. 5 Turn-On Time vs. Input Current

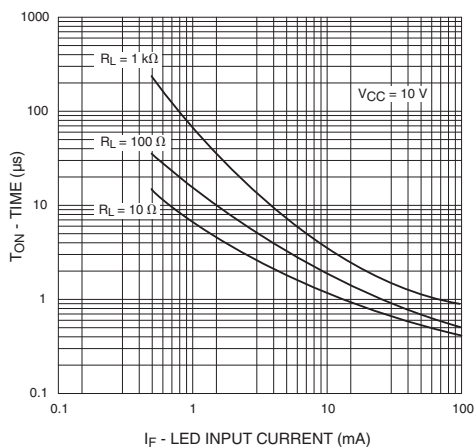
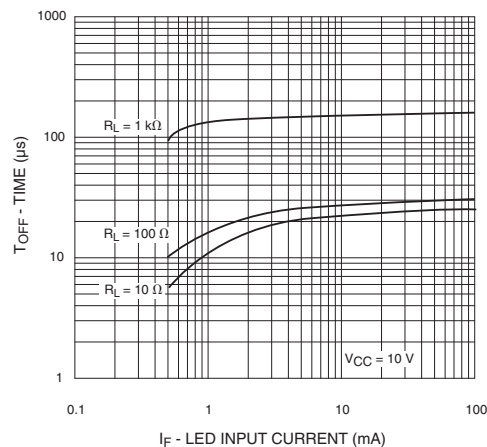


Fig. 6 Turn-Off Time vs. Input Current



CNX48U	H11B1	H11B2	H11B255	H11B3
MOC8080	TIL113			

TYPICAL ELECTRO-OPTICAL CHARACTERISTIC CURVES

(25°C Free air temperature unless otherwise specified) (Cont.)

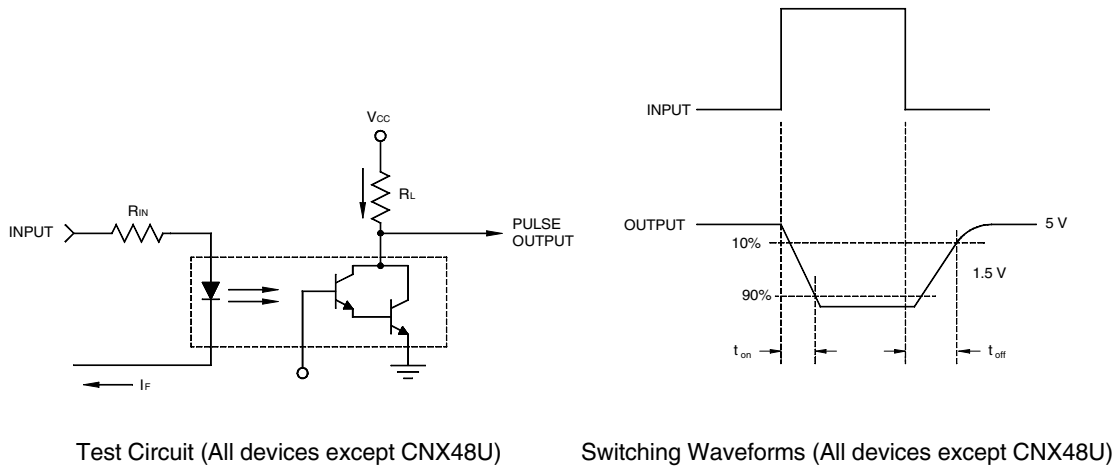


Fig. 7 Switching Time Test Circuit and Waveforms (All devices except CNX48U)

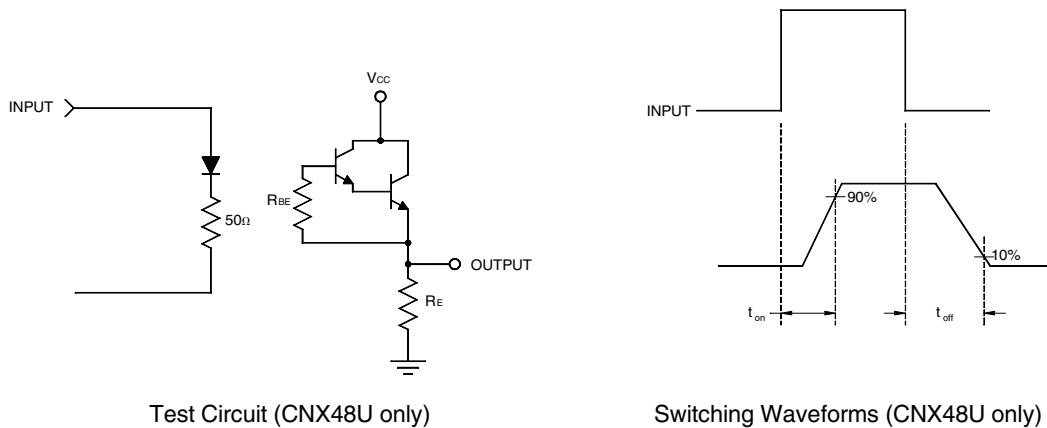


Fig. 8 Switching Time Test Circuit and Waveforms (CNX48U only)

Notes

1. The current transfer ratio (I_C/I_F) is the ratio of the detector collector current to the LED input current with V_{CE} @ 10 V.
2. For this test, LED pins 1 and 2 are common and phototransistor pins 4,5 and 6 are common.

Package Dimensions (Through Hole)

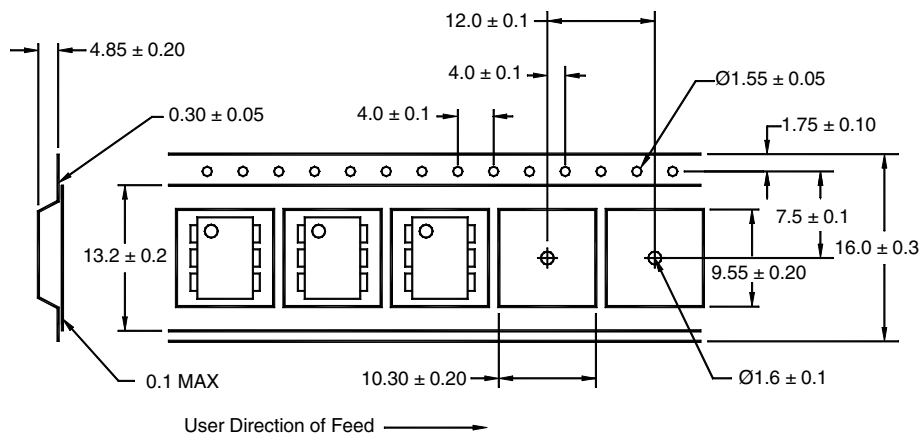


CNX48U	H11B1	H11B2	H11B255	H11B3
MOC8080	TIL113			

ORDERING INFORMATION

Option	Order Entry Identifier	Description
S	.S	Surface Mount Lead Bend
SD	.SD	Surface Mount; Tape and reel
W	.W	0.4" Lead Spacing
300	.300	VDE 0884
300W	.300W	VDE 0884, 0.4" Lead Spacing
3S	.3S	VDE 0884, Surface Mount
3SD	.3SD	VDE 0884, Surface Mount, Tape & Reel

QT Carrier Tape Specifications ("D" Taping Orientation)



NOTE

All dimensions are millimeters

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